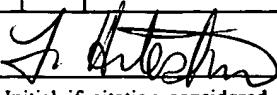
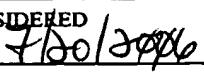


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Docket No. 04 JAN 2005

Sheet 1 of 1

Form PTO-1449 (REV. 8-83)			US Dept. of Commerce PATENT & TRADEMARK OFFICE <b>INFORMATION DISCLOSURE STATEMENT</b> (Use several sheets if necessary)		ATTY DOCKET NO. 122336		APPLICATION NO. New U.S. National Stage of PCT/JP03/08671	
					<b>APPLICANTS</b> Ryoji HOSHI et al.			
					<b>FILING DATE</b> January 4, 2005			
<b>U.S. PATENT DOCUMENTS</b>								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS	
FH.	1.	US 2002/0000189 A1	01/03/2002	Tadami TANAKA et al.				
<b>FOREIGN PATENT DOCUMENTS</b>								
		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB CLASS	
FH.	2.	JP-A-2000-044389 w/ abst. & trans.	02/15/2000	JAPAN				
↑	3.	JP-A-2001-151596 w/ abst. & trans.	06/05/2001	JAPAN				
	4.	JP-A-2000-219598 w/ abst. & trans.	08/08/2000	JAPAN				
	5.	WO 01/27362 A1 w/ abst.	04/19/2001	JAPAN				
	6.	JP-A-2001-274167 w/ abst. & trans.	10/05/2001	JAPAN				
	7.	JP-A-2002-012499 w/ abst. & trans.	01/15/2002	JAPAN				
↓	8.	JP-A-2000-109396 w/ abst. & trans.	04/18/2000	JAPAN				
FH.	9.	JP-A-2002-076007 w/ abst. & trans.	03/15/2002	JAPAN				
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>								
FH.	10.	Talid SINNO et al.; "Modeling Microdefect Formation in Czochralski Silicon"; <i>Journal of the Electrochemical Society</i> ; 146 (6); 1999; pp. 2300-2312.						
EXAMINER 					DATE CONSIDERED 			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

Date: January 4, 2005